10/516358 DT15 Rec'd PCT/PTO 24 NOV 2004

Attorney Docket No.: 15675P556 Express Mail No.: EV372845535US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

HACENE LAHRECHE, ET AL.

For: method for epitaxial growth of a gallium nitride film separated from its substrate

Mail Stop Patent Application Commissioner for Patents P.O, Box 1450 Alexandria, VA 22313-1450

## PRELIMINARY AMENDMENT

Dear Sir:

Please enter the following preliminary amendment for the present patent application.

## In the Specification:

After the title, please insert the following:

--The present patent application is a non-provisional application of International Application No. PCT/FR2003/001615, filed May 28, 2003.--

Respectfully submitted,

Blakely, Sokoloff, Taylor & Zafman LLP

Dated:

11/29/09

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